### PATENT ASSIGNMENT

### Electronic Version v1.1 Stylesheet Version v1.1

SUBMISSION TYPE:			NEW ASSIGNMENT		
NATURE OF CONVE	YANCE:		ASSIGNMENT		
CONVEYING PARTY	DATA				
		N	lame	Execution Date	]
OEG-TEG, LLC				03/19/2010	
RECEIVING PARTY D	DATA				
Name:	OEM Group I	nc.			
Street Address:	2120 W. Gua	dalupe	Road		
City:	Gilbert				
State/Country:	ARIZONA				
Postal Code:	85233				
Property Ty	уре		Number		
Application Number:		12203	0022		
Application Number:		10371	862		2203022
Application Number:		12552	664		
CORRESPONDENCE	DATA				
Fax Number:	(415)362 be sent via US		hen the fax attempt is unsuccessful.		CH \$1
Phone:	4153623				
Email:			fdml.com		
Correspondent Name:		-			
Address Line 1:			Street, 14th Floor		
Address Line 4:	San Fra	ncisco,	, CALIFORNIA 94108		
ATTORNEY DOCKET	NUMBER:		OEMG-00300US0		
NAME OF SUBMITTE	R:		Sheldon R. Meyer		
Total Attachments: 22					

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### FIRST AMENDMENT TO ASSET PURCHASE AGREEMENT

THIS FIRST AMENDMENT TO ASSET PURCHASE AGREEMENT (this "Amendment") is made and entered into as of April \_\_, 2010, and amends that certain Asset Purchase Agreement, dated as of March 19, 2010 (the "Original Agreement"), by and among Tegal Corporation, a Delaware corporation ("Tegal"), Sputtered Films, Inc., a California corporation and a wholly-owned subsidiary of Tegal ("SFI" and together with Tegal, "Sellers"), OEM Group Inc., an Arizona corporation ("OEM Group"), and OEG-TEG, LLC, an Arizona limited liability company ("Purchaser") (each Seller, OEM Group and Purchaser, a "Party" and collectively, the "Parties"). All capitalized terms which are used but not otherwise defined herein shall have the meanings specified to such terms in the Original Agreement.

### WITNESSETH:

WHEREAS, Sellers, OEM Group and Purchaser are parties to the Original

Agreement;

below.

WHEREAS, pursuant to Section 9.4 of the Original Agreement, the Parties may amend the Original Agreement by a writing signed by each of the Parties; and

WHEREAS, the Parties desire to amend the Original Agreement as set forth

NOW, THEREFORE, in consideration of the premises and of the mutual covenants and agreements contained herein and for other good and valuable consideration, the receipt and sufficiency of which are hereby acknowledged, the Parties, intending to be legally bound, hereby agree as follows:

Item 1 to Schedule 2.1.1(e). The Transferred Issued Patents.pdf referenced in 1.1 Item 1 of Schedule 2.1.1(e) to the Original Agreement is hereby amended and replaced in its entirety by substituting therefor the Transferred Issued Patents.pdf attached hereto as Annex 1.

Item 2 to Schedule 2.1.1(e). The Transferred Pending and Apps.pdf referenced in 1.2 Item 2 of Schedule 2.1.1(e) to the Original Agreement is hereby amended and replaced in its entirety by substituting therefor the Transferred Pending and Apps.pdf attached hereto as Annex 2.

Exhibit A to Exhibit G. Exhibit A to Exhibit G (the "Patent Assignment 1.3 Agreement") of the Original Agreement is hereby amended and replaced in its entirety by substituting therefor the Exhibit A to the Patent Assignment Agreement attached hereto as Annex 3.

Continued Force and Effect. Except as expressly provided herein, this 1.4 Amendment shall not constitute an amendment, modification or waiver of any provision of the Original Agreement or any rights or obligations of any Person under or in respect of the Original

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Agreement. Except as expressly amended herein, the provisions of the Original Agreement are and shall remain in full force and effect and are hereby ratified and confirmed. On and after the date hereof, each reference in the Original Agreement to "this Agreement" or the words "hereunder", "hereof", "herein" or words of similar import referring to the Original Agreement, shall mean and be a reference to the Original Agreement, as amended by this Amendment. This Amendment shall be subject to, shall form a part of, and shall be governed by, the terms and conditions set forth in the Original Agreement, as amended by this Amendment.

1.5 <u>Governing Law</u>. This Amendment shall be governed by and interpreted and enforced in accordance with the laws of the State of California, without regard to the conflicts of laws rules of such state. The rights and obligations of the parties under this Amendment shall not be governed by the provisions of the 1980 United Nations Convention on Contracts for the International Sale of Goods or the United Nations Convention on the Limitation Period in the International Sale of Goods, as amended.

1.6 <u>Counterparts</u>. This Amendment may be executed in any number of counterparts and any Party hereto may execute any such counterpart, each of which when executed and delivered shall be deemed to be an original and all of which counterparts taken together shall constitute but one and the same instrument. This Amendment shall become binding when one or more counterparts taken together shall have been executed and delivered by the parties. It shall not be necessary in making proof of this Amendment or any counterpart hereof to produce or account for any of the other counterparts.

1.8 <u>Severability</u>. Any provision of this Amendment which is invalid or unenforceable in any jurisdiction shall be ineffective to the extent of such invalidity or unenforceability without invalidating or rendering unenforceable the remaining provisions hereof, and any such invalidity or unenforceability in any jurisdiction shall not invalidate or render unenforceable such provision in any other jurisdiction.

1.9 <u>Headings</u>. All section headings contained in this Amendment are for convenience of reference only, do not form a part of this Amendment and shall not affect in any way the meaning or interpretation of this Amendment.

1.10 <u>Amendments and Waivers</u>. No amendment of any provision of this Amendment shall be valid unless the same shall be in writing and signed by each of the Parties.

[Signature page follows]

IN WITNESS WHEREOF, the Parties hereto have duly executed this Amendment as of the day and year first above written.

### **TEGAL CORPORATION**

By: \_\_\_\_\_ Name: Thomas R. Mika

Title: President and Chief Executive Officer

### SPUTTERED FILMS, INC.

By: \_\_\_\_\_ Name: Thomas R. Mika

Title: President and Chief Executive Officer

### **OEG-TEG, LLC**

By: Wayne Jeveli

Title: Manager

### OEM GROUP, INC.

By: Wayne Jeveli M. J. .

Title: President

[SIGNATURE PAGE TO FIRST AMENDMENT TO ASSET PURCHASE AGREEMENT]

### ANNEX 1

### TRANSFERRED ISSUED PATENTS.PDF OF ITEM 1 TO SCHEDULE 2.1.1(E) TO ASSET PURCHASE AGREEMENT

(see attached)

### ANNEX 2

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### TRANSFERRED PENDING AND APPS.PDF OF ITEM 2 TO SCHEDULE 2.1.1(E) TO ASSET PURCHASE AGREEMENT

(see attached)

### ANNEX 3

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### EXHIBIT A TO EXHIBIT G (PATENT ASSIGNMENT AGREEMENT) TO ASSET PURCHASE AGREEMENT (see attached)

### ACKNOWLEDGMENT

THIS ACKNOWLEDGMENT (this "<u>Acknowledgment</u>") is made and entered into as of this \_\_\_\_\_ day of April, 2010 by and among Tegal Corporation, a Delaware corporation ("<u>Tegal</u>"), Sputtered Films, Inc., a California corporation (together with Tegal, "<u>Assignors</u>") and OEG-TEG, LLC, an Arizona limited liability corporation ("<u>Assignee</u>")

WHEREAS, the Assignors and Assignee entered into that certain Patent Assignment dated as of March 19, 2010 (the "Patent Assignment").

WHEREAS, due to clerical error, an incorrect Exhibit A was previously attached to the Patent Assignment.

WHEREAS, the parties wish to clarify that the attached Exhibit A is the correct and complete Exhibit A to the Patent Assignment.

NOW THEREFORE, the undersigned hereby acknowledge and agree as follows:

1. The attached <u>Exhibit A</u> is the correct and complete <u>Exhibit A</u> to the Patent Assignment.

[SIGNATURE PAGE FOLLOWS]

IN WITNESS WHEREOF, Assignors have caused this Acknowledgment to be executed by their duly authorized representatives as of the day and year first above written.

**TEGAL CORPORATION** 

Name: Thomas R. Mika

Title: President and Chief Executive Officer

SPUTTERED FILMS, INC.

Name: Thomas R. Mika

Title: President and Chief Executive Officer

\_\_\_\_\_

ACKNOWLEDGEMENT:

STATE OF CALIFORNIA

COUNTY OF

) ) SS:

¥

On \_\_\_\_\_\_\_\_ before me \_\_\_\_\_\_\_, personally appeared \_\_\_\_\_\_\_\_ who proved to me on the basis of satisfactory

evidence to be the person(s) whose name(s) is/are subscribed to the within instrument and acknowledged to me that he/she/they executed the same in his/her/their authorized capacity(ies), and that by his/her/their signature(s) on the instrument the person(s), or the entity upon behalf of which the person(s) acted, executed the instrument.

I certify under PENALTY OF PERJURY under the laws of the State of California that the foregoing paragraph is true and correct.

WITNESS my hand and official seal.

(Seal)

Signature \_\_\_\_\_

SIGNATURE PAGE TO ACKNOWLEDGMENT

IN WITNESS WHEREOF, Assignee has caused this Acknowledgment to be executed by its duly authorized representatives as of the day and year first above written.

.....

	OEG-TEG, LLC
	Wayne M. Jeal.
	Name: <u>Wayne Jeveli</u>
	Title: Manager
ACKNOWLEDGEMENT:	
ARIZONA STATE OF CALIFORNIA	) ) SS:
COUNTY OF MARICOPA	)
on MAY 14+H	before me <u>Tohn S. Keller</u> personally appeared who proved to me on the basis of satisfactory
evidence to be the person(s) whe acknowledged to me that he/she and that by his/her/their signatu	ose name(s) is/are subscribed to the within institution and /they executed the same in his/her/their authorized capacity(ies), re(s) on the instrument the person(s), or the entity upon behalf of
which the person(s) acted, exect	uted the instrument.

I certify under PENALTY OF PERJURY under the laws of the State of California that the foregoing paragraph is true and correct.

WITNESS my hand and official seal.

Signature John S. Kuller



SIGNATURE PAGE TO ACKNOWLEDGMENT

### ACKNOWLEDGMENT

THIS ACKNOWLEDGMENT (this "Acknowledgment") is made and entered into as of this \_\_\_\_\_ day of April, 2010 by and among Tegal Corporation, a Delaware corporation ("Tegal"), Sputtered Films, Inc., a California corporation (together with Tegal, "Assignors") and OEG-TEG, LLC, an Arizona limited liability corporation ("Assignee")

WHEREAS, the Assignors and Assignee entered into that certain Patent Assignment dated as of March 19, 2010 (the "Patent Assignment").

WHEREAS, due to clerical error, an incorrect Exhibit A was previously attached to the Patent Assignment.

WHEREAS, the parties wish to clarify that the attached <u>Exhibit A</u> is the correct and complete <u>Exhibit A</u> to the Patent Assignment.

NOW THEREFORE, the undersigned hereby acknowledge and agree as follows:

1. The attached <u>Exhibit A</u> is the correct and complete <u>Exhibit A</u> to the Patent Assignment.

### [SIGNATURE PAGE FOLLOWS]

IN WITNESS WHEREOF, Assignors have caused this Acknowledgment to be executed by their duly authorized representatives as of the day and year first above written.

TEGAL CORPORATION

Name:	Thomas	<u>R.</u>	Mika		
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Title: President and Chief Executive Officer

SPUTTERED FILMS, INC.

Name: Thomas R. Mika

Title: President and Chief Executive Officer

**ACKNOWLEDGEMENT:** 

STATE OF CALIFORNIA

COUNTY OF

On April 23, 2010 before me Maur een E, MG0igan <u>Homas P, MKg</u> who proved to me on the basis of satisfactory evidence to be the person(s) whose name(s) are subscribed to the within instrument and acknowledged to me that the the the the the second the acknowledged to me that he she/they executed the same in his her/their authorized capacity(ies), and that by his her/their signature(s) on the instrument the person(s), or the entity upon behalf of which the person(s) acted, executed the instrument.

I certify under PENALTY OF PERJURY under the laws of the State of California that the foregoing paragraph is true and correct.

) SS:

WITNESS my hand and official seal.

signature Maureen E. Medligar



SIGNATURE PAGE TO ACKNOWLEDGMENT

IN WITNESS WHEREOF, the Parties hereto have duly executed this Amendment as of the day and year first above written.

### **TEGAL CORPORATION**

By:

Name: Thomas R. Mika

Title: President and Chief Executive Officer

### SPUTTERED FILMS, INC.

By:

Name: Thomas B. Mika

Title: President and Chief Executive Officer

### **OEG-TEG, LLC**

By: \_\_\_\_\_ Name: Wayne Jeveli

Title: Manager

### OEM GROUP, INC.

By: \_\_\_\_\_\_ Name: Wayne Jeveli

Title: President

[SIGNATURE PAGE TO FIRST AMENDMENT TO ASSET PURCHASE AGREEMENT]

EXHIBIT A TO THE PATENT ASSIGNMENT

Schedule 2.1.1(c) Transferred Intelectual Property

## ISSUED PATENTS TO BE TRANSFERRED

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Walter T Control     5.045 (15)     11115001       Walter T Control     5.015 (15)     9.017/2016     9.017/2016       ESC materoarce elimination     5.056 (15)     9.017/2016     9.017/2016       Heatledi Technication     5.156 (15)     9.00000     17.0019       Heatledi Technication     5.158 (15)     9.00000     17.0019       Escative sputtered Silv     7.158 (15)     9.00000     17.0010       Evaluation synthemation     5.153 (15)     9.00000     17.0000       Evaluation sputtered Silv     7.158 (15)     9.000000     17.0000       First Magnetion     5.153 (15)     9.000000     17.0000       First Magnetion     5.153 (15)     9.0000000     17.0000       First Magnetion     5.153 (15)     9.0000000     17.00000       First Magnetion     5.050 (15)     9.00000000     17.000000		0.452.280	11/1/2016	METHOD AND APPARATUS FOR ETCHING A SEMICONIZUCTOR WAFER WITH FEATURES HAVING VERTICAL SIDEVIALLS
Walter T Control     E.7.14.045     9.268/2018       ESC microsic elimination     6.106.025     8/17/2018       ESC microsic elimination     6.106.025     8/17/2018       FESC microsic elimination     6.106.025     8/17/2018       FESC microsic elimination     6.106.025     8/17/2018       Festeled Tertured H/Fe surfaces     2.458.000     1/2/2019       Stop on Alumina 1     2.158.000     0.02/2014       Stop on Alumina 1     2.173.200     0.02/2014       Stop on Alumina 1     2.173.200     0.02/2014       Stop on Alumina 1     2.271.122     0.02/2014       Stop on Alumina 1     0.02/2014     0.02/2014       Stop on Alumina 1	OL.010711300 Water Y Control	\$249.116	110/08/111	A METHOD FOR MINIMIZING THE ORTICAL DIMENSION GROWTH OF A FEATURE ON A SEMICONDUCTOR WARER
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EXHIBIT A TO THE PATENT ASSIGNMENT

Schedule 2.1.1(e) Transferrød Intellectual Property

# TRANSFERRED PENDING PATENTS AND PATENT APPLICATIONS

Docket No.	Description	Count		App. No.	Trike
TEGL-01005EP0	MRe source EP	65	1/23/1667	97807537.1	PLASMA ETCH REACTOR AND METHOD
TEOL-010090W1	HPR for surging fame	8	1/23/1/387	200410008859.4	PALASMA ETOH REACTOR AND METHOD FOR EMEROING FILMS
TEGL-ChOOREPO	Affe for empire fifthe	6	1/2/3/1667	97303340.4	PLASMA ETCH REACTOR AND METHOD FOR EMERGING FILMS
TEGL-01000-003	HRe for emigning films	9	1423/1997	10-504062	PALASMA ETOH REACTOR AND METHOD FOR EMEROING FILMS
TEGL-01021EP0	HRefEimigng film etch	6 <u>0</u>	1031/021	97903805.4	REPERTING AND APPARATING FOR ETCHING & SERVICIONOLOGY WARREN
	\$ \$				MAPROVED METHOD & APPARATUS FOR ETCHING A SERVICINDUCTOR WAFER WITH
TEGL.01021.JPO	HReffingus tim etch	Q;	103/1027	10-504081	FEATURES HAVINO VERTICAL SUSEVALLS
TEOL-010926P0	Heated/fextured HR/s surfaces	din Lin	11/21/2000	980631,5	REACTOR WITH HEATED AND TEXTURED FLECTRODES AND SURPACES
TEGL.01052.PO	Hested Textured HRe surfaces	Q;	11/21/2000	2001-542603	MAPROVED REACTOR WITH HEATED AND TEXTURED ELECTRODES AND SURPACES
TEOL-010920/92	Heated/fextured HR/s surfaces	33	80,022,058	12/203,002	REACTOR WITH HEATED AND TEXTURED FLECTRODES AND SURPACES
1201.0120820	Reactive scittered Silva	89	514 212004	4762786	DEPOSITION APPARATUS AND METHOD
TEGL-01209.870	Reactive sputtered SN4X	ŝ,	51122204	2006-533061	DEPOSITION APPARATUS AND METHOD
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TEGL-01249030	Magnetron wAdjustable Tanget	99 19	0/21/2003	10/5/1, 252 (20040103952)	MAGNETRON NETH ADJUNTARI,E TARGET POSITRAMMO
Tegs/50020350	Physica distriction of the physical states of	99 19	3/27/2667	US 11/863.046 (2026003011)	HIGH ADHESIVE BACKSIDE METALLIZATION
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					SYSTEM AND METHOD FOR PROCESSING A WAFER INCLUDING STOP ON ALUMINUM
TEGL-01172.JP0	Stop on Aurrina1	Q;	3/9/2008	2007-531406	PROCESSING
					DRY ETCH STOP PROCESS FOR ELIMINATING ELECTRICAL SHORTING IN MRAM DEVICE
TEGL.01247.JP0	Stop on Aumins2	Q;	3/16/2007	2009-500499	STRUCTURES
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### PATENT ASSIGNMENT

**THIS PATENT ASSIGNMENT** (this "<u>Assignment</u>") is made and entered into as of this 19th day of March, 2010 ("<u>Effective Date</u>") by and among Tegal Corporation, a Delaware corporation ("<u>Tegal</u>"), Sputtered Films, Inc., a California corporation (together with Tegal, "<u>Assignors</u>") and OEG-TEG, LLC, an Arizona limited liability corporation ("<u>Assignee</u>"). Capitalized terms not otherwise defined herein shall have the meanings assigned to such terms in the Purchase Agreement (as defined below).

### WITNESSETH:

WHEREAS, Assignors and Assignee are parties to that certain Asset Purchase Agreement, dated March 19, 2010 (the "<u>Purchase Agreement</u>"), pursuant to which Assignee has acquired all of Assignors' right, title and interest in and to certain patents and patent applications as listed on <u>Exhibit A</u> hereto (the "<u>Assigned Patents</u>");

WHEREAS, to effect the transfer of the Assigned Patents as contemplated in the Purchase Agreement, Assignors and Assignee desire to enter into this Assignment;

NOW, THEREFORE, for good and valuable consideration, the receipt and sufficiency of which is hereby acknowledged, Assignors and Assignee each hereby agree as follows:

1. <u>Assignment</u>. Assignors hereby sell, assign, transfer, convey and deliver to Assignee and its successors and assigns, and Assignee hereby purchases and accepts from Assignors, all of Assignors' right, title and interest in, to and under the Assigned Patents, and to any continuations, continuations-in-part, divisionals, renewals, substitutes, reexaminations and reissues thereof and foreign counterparts thereto, and all patents issuing therefrom, together with all priority rights under any international conventions and treaties, and the right to sue and recover damages for future or past infringements of the Assigned Patents and to fully and entirely stand in the place of Assignors in all matters related thereto.

2. <u>Further Assurances</u>. Assignors agree to execute and deliver such other documents and to take all such other actions as Assignee, its successors and assigns may reasonably request to effect the terms of this Assignment and to execute and deliver any and all affidavits, testimonies, declarations, oaths and other documentation as may be reasonably required to effect the terms of this Assignment. Assignee, or its successor or assign, as the case may be, shall be responsible for all costs incurred by Assignors in executing and delivering any of the foregoing.

3. <u>Authorization</u>. Assignors hereby authorize and request the Commissioner of Patents and Trademarks of the United States, and, in the case of any patent applications filed with any office of any country or countries foreign to the United States, any officer of such country whose duty it is to issue patents or other evidence or forms of intellectual property protection or applications as aforesaid, to issue the same to Assignee and its successors, assigns and other legal representatives in accordance with the terms of this Assignment.

PATENT REEL: 024551 FRAME: 0032

SV\712945.4

4. <u>Miscellaneous</u>. This Assignment may not be supplemented, altered or modified in any manner except by a writing signed by all parties hereto. The failure of any party to enforce any terms or provisions of this Assignment shall not waive any of its rights under such terms or provisions. This Assignment shall bind and inure to the benefit of the respective parties and their assigns, transferees and successors. This Assignment and any amendments hereto may be executed in one or more counterparts, each of which shall be deemed an original but all of which together will constitute one and the same instrument.

### [SIGNATURE PAGE FOLLOWS]

**IN WITNESS WHEREOF,** Assignors have caused this Assignment to be executed by their duly authorized representatives as of the Effective Date.

TEGAL CORPORATION

Name: Thomas R. Mika

Title: President and Chief Executive Officer

SPUTTERED FILMS, INC.

Name: Thomas R. Mika\_\_\_\_

Title: President and Chief Executive Officer

**ACKNOWLEDGEMENT:** 

STATE OF CALIFORNIA	)	
COUNTY OF Some	) SS:	
On 3/14/10	before me <u>Copression WEXX</u> Light, personally appeare who proved to me on the basis of satisfactor	h
THOMAS R. MIKA	who proved to me on the basis of satisfacto	ory

evidence to be the person(s) whose name(s) is/are subscribed to the within instrument and acknowledged to me that he/she/they executed the same in his/her/their authorized capacity(ies), and that by his/her/their signature(s) on the instrument the person(s), or the entity upon behalf of which the person(s) acted, executed the instrument.

I certify under PENALTY OF PERJURY under the laws of the State of California that the foregoing paragraph is true and correct.

WITNESS my hand and official seal.

Signature \_\_\_\_\_

**CJ BRANDMEYER** COMM. #1793738 ์ ปี 0 NOTARY PUBLIC-CALIFORNIA SONOMA COUNTY My Comm. Expires March 16, 2012 (Seal)

[Signature Page to Patent Assignment]

**IN WITNESS WHEREOF,** Assignee has caused this Assignment to be executed by its duly authorized representatives as of the Effective Date.

**OEG-TEG, LLC** 

Name:	Wayne Jeveli

Title: Manager

**ACKNOWLEDGEMENT:** 

STATE OF CALIFORNIA ) SS: COUNTY OF Source ) On <u>3/19/10</u> before me<u>Cimulation</u>, personally appeared <u>WAYNE JEVEL(</u> who proved to me on the basis of satisfactory evidence to be the person(s) whose name(s) is/are subscribed to the within instrument and

evidence to be the person(s) whose name(s) is/are subscribed to the within instrument and acknowledged to me that he/she/they executed the same in his/her/their authorized capacity(ies), and that by his/her/their signature(s) on the instrument the person(s), or the entity upon behalf of which the person(s) acted, executed the instrument.

I certify under PENALTY OF PERJURY under the laws of the State of California that the foregoing paragraph is true and correct.

WITNESS my hand and official seal.

Signature

(Seal)

CJ BRANDMEYER COMM. #1793738 ARY PUBLIC-CALIFORNIA SCNOMA COUNTY ornm. Expires March 16, 2012

[Signature Page to Patent Assignment]

EXHIBIT A

AGREEMENT
ASSIGNMENT
<b>HE PATENT</b>
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### Schedule 2.1.1(d) Transferred Intellectual Property

## **ISSUED PATENTS TO BE TRANSFERRED**

Docket No. Description	Pat No.	Expire date	Trie
3CN0	84001	3/28/2016	INTEGRATED SEMICONDUCTOR WAFER PROCESSING SYSTEM
	826231	3/28/2016	INTEGRATED SEMICONDUCTOR WAFER PROCESSING SYSTEM
TEGL-01003FR0 Rinse/Strip/Rinse	826231	3/28/2016	INTEGRATED SEMICONDUCTOR WAFER PROCESSING SYSTEM
TEGL-01003JP0 Rinse/Strip/Rinse	3686678	3/28/2016	INTEGRATED SEMICONDUCTOR WAFER PROCESSING SYSTEM
TEGL-01003KR0 Rinse/Strip/Rinse	441637	3/28/2016	INTEGRATED SEMICONDUCTOR WAFER PROCESSING SYSTEM
TEGL-01003US0 Rinse/Strip/Rinse	5.672.239	5/10/2015	INTEGRATED SEMICONDUCTOR WAFER PROCESSING SYSTEM
	5.985.089	11/16/2016	PLASMA ETCH SYSTEM
TEGL-01004US1_ICP Stripper Source	5.958,139	5/25/2015	
	6.120.610	5/25/2015	PLASMA ETCH SYSTEMCONTINUATION APPLICATION
TEGL-01008CN0 HRe source	ZL97197274.5	1/23/2017	PLASMA ETCH REACTOR AND METHOD
TEGL-01008KR0 HRe source	453538	1/23/2017	PLASMA ETCH REACTOR AND METHOD
TEGL-01008US5 HRe source	6.500.314	7/3/2016	PLASMA ETCH REACTOR AND METHOD
TEGL-01008US6 HRe source	6,620,335	7/3/2016	PLASMA ETCH REACTOR AND METHOD
TEGL-01008US7 HRe source	6,354,240	9/11/2018	PLASMA ETCH REACTOR HAVING A PLURALITY OF MAGNETS
TEGL-01008US8 HRe source	6,905,969	3/5/2017	PLASMA ETCH REACTOR AND METHOD
TEGL-01008US9 HRe source	7,223,699	7/3/2016	PLASMA ETCH REACTOR AND METHOD
TEGL-01009CN0 HRe for emrgng films	ZL97197108.0	1/23/2017	PLASMA ETCH REACTOR AND METHOD FOR EMERGING FILMS
TEGL-01009CN2 HRe for emrang films	200410003858.X	1/23/2017	PLASMA ETCH REACTOR AND METHOD FOR EMERGING FILMS
TEGL-01009KR0 HRs for emigrid films	528733	1/23/2017	PLASMA ETCH REACTOR AND METHOD FOR EMERGING FILMS
	6.048,435	7/3/2016	PLASMA ETCH REACTOR AND METHOD FOR EMERGING FILMS
TEGL-01009US1 HRe for emrang films	6,410,448	7/3/2016	PLASMA ETCH REACTOR AND METHOD FOR EMERGING FILMS
	6,190,496	7/3/2016	PLASMA ETCH REACTOR AND METHOD FOR EMERGING FILMS
			IMPROVED METHOD AND APPARATUS FOR ETCHING A SEMICONDUCTOR WAFER WITH FEATURES HAVING VERTICAL
TEGL-01021CN0 HRe/Emrgng film etch	ZL97197232.X	1/23/2017	SIDEWALLS
TEGL-01021KR0 HRe/Emrgng film etch	537231	1/23/2017	METHOD AND APPARATUS FOR ETCHING A SEMICONDUCTOR WAFER
TEGL-01021US0 HRe/Emigng film etch	6,127.277	7/3/2016	METHOD AND APPARATUS FOR ETCHING A SEMICONDUCTOR WAFER WITH FEATURES HAVING VERTICAL SIDEWALLS
			A DESTRUCTION OF
	0487.780	91.07/1./1	METHOD AND ANYAKATON FOR FLORING A DEMICIONUO IN WAYEN WYEN YATO FEATURES ANYAKING VERTIGATION ANYAKING VERTIGA
	<u>6,046,116</u>	11/19/2017	A METHOU FOR MINIMURNS. HE CRITICAL UNMENSION GROWTH OF A FEATURE ON A SEMICONDUCTOR VAFER
	<u>5,774,046</u>	9/28/2018	WE HOD FOR MINIMIZING THE CRITICAL DIMENSION GROWTH OF A FEATURE ON A SEMICUNDUCTOR WAFER
	123764	12/1/2018	PLASMA REACTOR WITH A DEPOSITION SHIELD (TEXT INCLUDES U.S. 1073 & 1073CIP1)
	6,006,694	12/5/2017	PLASMA REACTOR WITH A DEPOSITION SHIELD
	<u>6,360,685</u>	12/5/2017	PLASMA REACTOR WITH A DEPOSITION SHIELD
TEGL-01073US3 ICP deposition shield	6.173.674	12/5/2017	PLASMA REACTOR WITH A DEPOSITION SHIELD
TEGL-01073US4_ICP deposition shield	6.170.431	12/5/2017	PLASMA REACTOR WITH A DEPOSITION SHIELD
TEGL-0107SUS5 ICP deposition shield	6.521.081	12/5/2017	DEPOSITION SHIELD FOR A PLASMA REACTOR
TEGL-01082CND Oxidized HM during Etch	ZL99803212.3	1/5/2019	METHOD FOR USING A HARD MASK FOR CRITICAL DIMENSION GROWTH CONTAINMENT
	538839	1/5/2019	METHOD FOR USING A HARD MASK FOR CRITICAL DIMENSION GROWTH CONTAINMENT
	<u>6.287.975</u> 6.258.975	1/20/2018	METHOD FOR USING A HARD MASK FOR CHILICAL DIMENSION GROWTH CONTAINMENT METHOD FOR USING A HARD MASK FOR CHILICAL DIMENSION GROWTH CONTAINMENT
TEGL-UTUSZUSZ OXIQIZEG HM GUTING ETCH TEGL 010001153 OXI4102 UM AUTING ETCH	0.338.250	1//2///2018	METHOU FOR USING A FARD MASN FOR YATHOAL UMBENSION GROWFIT CONTAINMENT METHOD FOR LIGNIG & HARDI MASK FOR CRITICAL DIMENSION GROWFIT CONTAINMENT
	7771.027	0000000000	

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THE THE MALE AND APPARATUS FOR MINIMIZING SEMICONDUCTOR WAFER ARCING DURING SEMICONDUCTOR WAFER PROCESSING METHOD AND APPARATUS FOR MINIMIZING SEMICONDUCTOR WAFER ARCING DURING SEMICONDUCTOR WAFER METHOD AND APPARATUS FOR MINIMIZING SEMICONDUCTOR WAFER ARCING DURING SEMICONDUCTOR WAFER METHOD AND APPARATUS FOR MINIMIZING SEMICONDUCTOR WAFER ARCING DURING SEMICONDUCTOR WAFER SEACOFS WITH HEATED AND TEXTURED ELECTRODES AND SURFACES COBALT SILICIDE ETCH PROCESS AND APPARATUS REACOFS WITH HEATED AND TEXTURED DIA WAFER TO AN ELECTRICAL COMPONENT OR SUB- ASSEMINATING SURFACES AND APPARATUS COBALT SILICIDE ETCH PROCESS AND APPARATUS COBALT SILICIDE ETCH PROCESS AND APPARATUS COBALT SILICIDE ETCH PROCESS AND APPARATUS SYSTEM FOR, AND METHOD OF ETCHING A SUFFACE ON A WAFER METHOD OF DEPOSITING MATERIALS ON A WAFER APPARATUS FOR, AND METHOD OF ETCHING A SUFFACE ON A WAFER APPARATUS FOR AND METHOD OF ETCHING A SUBSTRATE APPARATUS FOR AND METHOD OF ETCHING A SUBSTRATE DUAL DEGASOCOL LOADLOCK CLUSTER TOOL DUAL DEGASOCOL LOADLOCK CLUSTER TOOL UNAL DEGASOCOL LOADLOCK CLUSTER TOOL DUAL DEGASOCOL LOADLOCK CLUSTER TOOL UNTH A ANDLROLK CLUSTER TOOL DUAL DEGASOCOL LOADLOCK CLUSTER TOOL UNAL DEGASOCOL LOADLOCK CLUSTER TOOL	
ISSU Expire date Title 8/17/2018 MET 8/17/2018 PRO 12/2019 PRO 12/2019 PRO 12/2019 PRO 12/2019 PRO 12/2019 PRO 10/6/2019 PRO 10/6/2019 PRO 10/6/2019 PRO 10/6/2020 PUA 7/2/2016 APP 7/2/2016 APP 7/2/2016 DUA 10/6/2020 DUA 10/6/2020 DUA 10/6/2020 DUA 10/6/2020 DUA	
Pat. No.       6.346.428     6.346.428       6.46.925     6.469.069       7.179.350     7.179.350       7.273.508     9.47       6.065.198     6.069       7.270.729     6.092       6.055.198     6.069       6.055.198     6.055       6.055.198     6.055       7.275.556     6.055       6.525.1656     6.654       6.622.1641     6.555       6.522.1656     6.654	
Docket No.DescriptionPat. No.TEGL-01083US1ESC microarc elimination6.346.428TEGL-01083US1ESC microarc elimination6.346.428TEGL-01083US2ESC microarc elimination6.346.428TEGL-01023US1Heated/Textured HRe surfaces6.406.925TEGL-01023US1Heated/Textured HRe surfaces6.406.925TEGL-01023US1Heated/Textured HRe surfaces6.406.925TEGL-01023US1Heated/Textured HRe surfaces6.406.925TEGL-0122US0Reactive sputtered Shtk7.179.350TEGL-01212US0Nuface etching system and method7.467.598TEGL-01212US0NvD Apparatus6.005.498TEGL-01212US0NvD Apparatus7.312.256TEGL-01212US0Pydrocartron temoval system and method6.025.656TEGL-01212US0Degast/Loadlock Cluster tool6.256.656TEGL-01212US0Magnetron wtControlled dc pwr6.824.653	

## EXHIBIT A TO THE PATENT ASSIGNMENT AGREEMENT

### Schedule 2.1.1(d) Transferred Intellectual Property

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**EXHIBIT A TO THE PATENT ASSIGNMENT** 

### Schedule 2.1.1(e) Transferred intellectual Property

# TRANSFERRED PENDING PATENTS AND PATENT APPLICATIONS

Docket No.	Description	Country	try App. Date	App. No.	Title
TEGL-01008EP0	HRe source	â	1/23/1997	97907537.1	PLASMA ETCH REACTOR AND METHOD
TEGL-01009CN1	HRe for emigrid films	NO	1/23/1997	200410003859.4	PLASMA ETCH REACTOR AND METHOD FOR EMERGING FILMS
TEGL-01009EP0	HRe for emigno films	с Ш	1/23/1997	97903910,4	PLASMA ETCH REACTOR AND METHOD FOR EMERGING FILMS
TEGL-01009JP0	HRe for emrang films	<u>0</u> -	1/23/1997	10-504082	PLASMA ETCH REACTOR AND METHOD FOR EMERGING FILMS
TEGL-01021EP0	HRe/Emrang film etch	ß	1/23/1997	97903905.4	METHOD AND APPARATUS FOR ETCHING A SEMICONDUCTOR WAFER
	5				IMPROVED METHOD & APPARATUS FOR ETCHING A SEMICONDUCTOR WAFER WITH
TEGL-01021JP0	HRe/Emigng film etch	<u>a</u> ,	1/23/1997	10-504081	FEATURES HAVING VERTICAL SIDEWALLS
TEGL-01092EP0	Heated/Textured HRe surfaces	с Ш	11/21/2000	980631.6	REACTOR WITH HEATED AND TEXTURED ELECTRODES AND SURFACES
TEGL-01092JP0	Heated/Textured HRe surfaces	<u>α</u> .,	11/21/2000	2001-542603	IMPROVED REACTOR WITH HEATED AND TEXTURED ELECTRODES AND SURFACES
TEGL-01092US2	Heated/Textured HRe surfaces	SU	9/2/2008	12/205,022	REACTOR WITH HEATED AND TEXTURED ELECTRODES AND SURFACES
TECL-01209EPO	Reactive sputtered SiNx	Q. LUJ	5/12/2004	4752195	DEPOSITION APPARATUS AND METHOD
TEOL-01209JP0	Resolive sputtered SiNk	<u>A</u>	5/12/2004	2006-533061	DEPOSITION APPARATUS AND METHOD
TEGL-01218.0P0	Deges/Loadkock Olusier tool	<u>0</u> ,	7/2/2001	2002-507709	DUAL DEGASICOOL LOADLOOK OLUSTER TOOL
TEGL-01243US0	Magnetron wArijustable Targel	5	2/21/2003	10/371,862 (20040163952)	MAGNETRON WITH ADJUSTABLE TARGET POSITIONING
Tecals002US0	High withesive backside melalization	2	9/27/2007	US 11/643.046 (2008/0/83611)	HIGHADHESVE BACKSIDE METALLIZATION
Tegal3004a	Stress adjustment in reactive sputtering	90	3/25/2009	20090242392 US 61/039,348	STRESS ADJUSTMENT IN REACTIVE SPUTTERING
Tegai3004b	Stress adjustment in readive sputtering	00	3/26/2003	20090242388 US 61/039,349	STRESS ADJUSTMENT IN REACTIVE SPUTTERING
Tecal3005	Stress control in reactive sputtering	ŝ	5/11/2009 PROV	US 61/039,354 12/411369	Control of crystal orientation and stress in sputter deposited that films
Tegat3008	SICr PVD preent (Valery)	30	3/25/2009	US20090246386 01/130884	Sputter deposition of cermet reastor films with low TCR
2					SYSTEM AND METHOD FOR PROCESSING A WAFER INCLUDING STOP-ON-ALUMINUM
TEGL-01172JP0	Stop on Alumina1	<u>م</u>	9/9/2005	2007-531406	PROCESSING
					DRY ETCH STOP PROCESS FOR ELIMINATING ELECTRICAL SHORTING IN MRAM DEVICE
TEGL-01247JP0	Stop on Alumina2	₽,	3/16/2007		STRUCTURES DRY ETCH STOP PROCESS FOR FI IMINATING FI ECTRICAL SHORTING IN MBAM DEVICE
TEGL-01247US2	Stop on Alumina2	SU	12/14/2009		STRUCTURES